# EPSON

# SED157A Series Dot Matrix LCD Driver

- Support up to 65×224 Display
  Duits in Douter Supply Circuit for LC
- Built-in Power Supply Circuit for LCD

## ■ OVERVIEW

The SED157A Series is a single-chip dot matrix liquid crystal display driver that can be connected directly to a microprocessor bus. Eight-bit parallel or serial display data transmitted from the microprocessor is stored in the internal display data RAM, and the chip generates liquid crystal drive signals, independently of the microprocessor.

It has a on-chip  $65 \times 256$ -bit display data RAM, and there is a one-to-one correspondence between the dot pixel on the liquid crystal panel pixels and internal RAM bit. This feature ensures implementation of highly free display.

The SED157A Series incorporate 65 common output circuits and 224 segment output circuits. A single chip can drive a  $65 \times 224$  dot display (capable of displaying 14 columns  $\times$  4 rows with 16  $\times$  16-dot kanji font). Further, display capacity can be extended by designing two chips in a master/display configuration.

The SED157A Series can read and write RAM data with the minimum current consumption because it does not require any external operation clock. Also it incorporates a LCD power supply featuring a very low current consumption, a LCD drive power voltage regulator resistor and a display clock CR oscillator circuit. This allows the display system of a high-performance for handy equipment to be realized at the minimum power consumption and minimum component configuration.

## ■ FEATURES

- Direct display of RAM data using the display data RAM
  - RAM bit data "1" ..... goes on.

"0" ..... goes off (at display normal rotation).

- RAM capacity
- $65 \times 256 = 16,640$  bits
- Liquid crystal drive circuit
  65 circuits for the common output and 224 circuits for the segment output
- High-speed 8-bit MPU interface (Both the 80 and 68 series MUPs can directly be connected.)/serial interface enabled
- Abundant command functions

Display Data Read/Write, Display ON/OFF, Display Normal Rotation/Reversal, Page Address Set, Display Start Line Set, column address set, Status Read, Power Supply Save Display All Lighting ON/OFF, LCD Bias Set, Read Modify Write, Segment Driver Direction Select, Electronic Control, V5 Voltage Adjusting Built-in Resistance Ratio Set, Static Indicator, n Line Alternating Current Reversal Drive, Common Output State Selection, and Built-in Oscillator Circuit ON

• Built-in static drive circuit for indicators (One set, blinking speed variable)

## **SED157A Series**

- Built-in power supply circuit for low power supply liquid crystal drive Booster circuit (Boosting magnification - double, triple, quadruple, boosting reference power supply external input enabled)
- 3% high accuracy alternating current voltage adjusting circuit (Temperature gradient: -0.05%/°C)
  Built-in V5 voltage adjusting resistor, built-in V1 to V4 voltage generation split resistors, built-in electronic control function, and voltage follower
- Built-in CR oscillator circuit (external clock input enabled)
- Ultra-low power consumption
- Power supplies

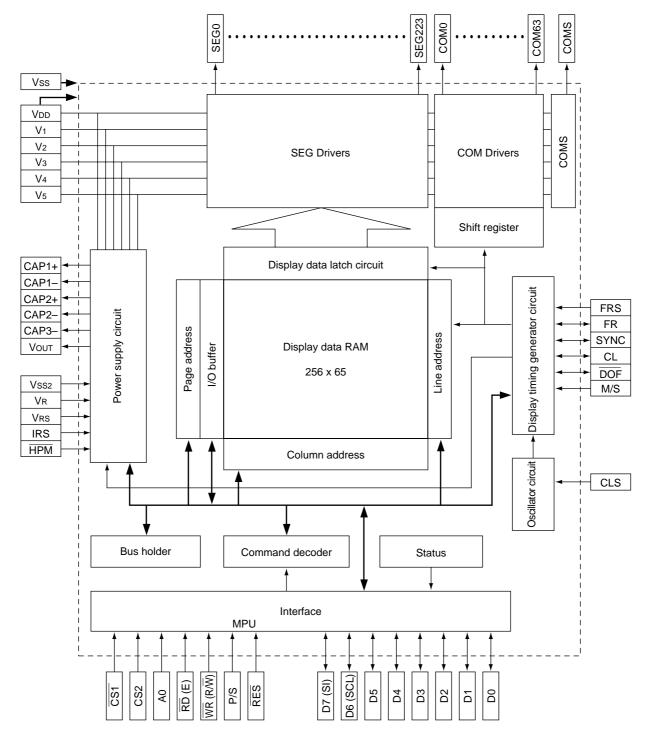
Logic power supply: VDD - VSS = 1.8 to 5.5 V Boosting reference power supply: VDD - VSS = 1.8 to 6.0 V Liquid crystal drive power supply: V5 - VDD = -4.5 to -18.0 V

- Wide operating temperature range -40 to 85°C
- CMOS process
- Shipping form Bare chip, TCP
- No light-resistant and radiation-resistant design are provided.

#### Series specification

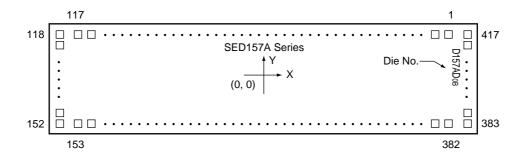
Product name	Duty	Bias	SEG Dr	COM Dr	VREG temperature gradient	Shipping form
SED157AD0B	1/65	1/9, 1/7	224	65	−0.05%/°C	Bare chip
SED157ATo*	1/65	1/9, 1/7	224	65	−0.05%/°C	TCP

## BLOCK DIAGRAM



## ■ PIN ASSIGNMENT

Chip Specification



	Item	x	Size	Y	Unit
Chip size		16.65	×	2.90	mm
Chip thickne	SS		0.625		mm
Bump pitch			69 (Min.)		μm
Bump size	PAD No.1 to 117	85	×	85	μm
	PAD No.118	85	×	73	μm
	PAD No.119 to 151	85	×	47	μm
	PAD No.152	85	×	73	μm
	PAD No.153	73	×	85	μm
	PAD No.154 to 381	47	×	85	μm
	PAD No.382	73	×	85	μm
	PAD No.383	86	×	73	μm
	PAD No.384 to 416	85	×	47	μm
	PAD No.417	85	×	73	μm
Bump heigh	t		17 (Typ.)		μm

## **EPSON**

## ■ PIN DESCRIPTION

Power Supply Pin

Pin name	I/O	Description	Number of pins
Vdd	Power supply	Commonly used with the MPU power supply pin Vcc.	12
Vss	Power supply	0 V pin connected to the system ground (GND)	9
VSS2	Power supply	Boosting circuit reference power supply for liquid crystal drive	5
Vrs	Power supply	External input pin for liquid crystal power supply voltage adjusting circuit They are set to OPEN	2
V1, V2 V3, V4 V5	Power supply	Multi-level power supply for liquid crystal drive. The voltage specified according to liquid crystal cells is impedance-converted by a split resistor or operation amplifier (OP amp) and applied. The potential needs to be specified based on VDD to establish the relationship of dimensions shown below:	10
		$\begin{array}{c} \text{VDD} (=\!V0) \geq V1 \geq V2 \geq V3 \geq V4 \geq V5 \\ \text{Master operation}  \text{When the power supply is ON, the following voltages are applied to V1 ~ V4 from the built-in power supply circuit. The selection of the voltages is determined using the LCD bias set command. \\ \hline V1 & 1/9 \cdot V5 & 1/7 \cdot V5 \\ V2 & 2/9 \cdot V5 & 2/7 \cdot V5 \\ V3 & 7/9 \cdot V5 & 5/7 \cdot V5 \\ V4 & 8/9 \cdot V5 & 6/7 \cdot V5 \end{array}$	

## • LCD Power Supply Circuit Pin

Pin name	I/O	Description	Number of pins
CAP1+	0	Boosting capacitor positive side connecting pin. Connects a capacitor between the pin and CAP1– pin.	2
CAP1-	0	Boosting capacitor negative side connecting pin. Connects a capacitor between the pin and CAP1+ pin.	2
CAP2+	0	Boosting capacitor positive side connecting pin. Connects a capacitor between the pin and CAP2– pin.	2
CAP2-	0	Boosting capacitor negative side connecting pin. Connects a capacitor between the pin and CAP2+ pin.	2
CAP3–	0	Boosting capacitor negative side connecting pin. Connects a capacitor between the pin and CAP1+ pin.	2
Vout	0	Boosting output pin. Connects a capacitor between the pin and Vss2.	2
VR	Ι	Voltage adjusting pin. Applies voltage between VDD and V5 using a split resistor. Valid only when the V5 voltage adjusting built-in resistor is not used (IRS="L") Do not use VR when the V5 voltage adjusting built-in resistor is used (IRS="H")	1

## • System Bus Connecting Pins

Pin name	I/O			Descriptio	n			Number of pins
D7 to D0 (SI) (SCL)	I/O	MPU data bus When the seria D7: Serial da D6: Serial clo In this case, D	al interface is ta entry pin (S ock input pin ( 0 to D5 are se	selected (P/S SI) SCL) et to high impe				8
AO	I	discriminate da A0="H": Indic	ata / comman ates that D0 t			connected to		1
RES	Ι	Initialized by se Reset operation	etting RES to n is performe	"L". d at the RES	signal level.			1
CS1 CS2	I		nal. When C	S1="L" and C	S2="H", this sig	nal becomes a	ctive	2
RD (E)	I	When the 80  Pin that conn  the SED157A	series M <u>PU</u> i ects the RD s series data b series MPU i	s connected, a signal of the 80 ous is set in the s connected, a	active "L" is set. ) series MPU. V e output state. active "H" is set	Vhen this signa	al is "L",	1
WR (R/W)	I	Pin that conn	ects the WR s e leading edg series MPU is ontrol signal ir ad operation	signal of <u>the</u> 8 e of the WR s s connected,	active "L" is set. 0 series MPU. ignal.		ignal is	1
FRS	0	Output pin for Used together	static drive with the SYN	C pin				1
C86	I	MPU interface C86="H": 68 C86="L": 80 s	series MPU ir	nterface				1
P/S	I	P/S="H": Paral P/S="L": Serial	Switching pin for parallel data entry/serial data entry P/S="H": Parallel data entry P/S="L": Serial data entry According to the P/S state, the following table is given.					
		P/S	Data/ command	Data	Read/write	Serial clock		
		"H"	A0	D0 to D7	$\overline{RD}, \overline{WR}$			
		"L"	A0	SI (D7)	Write-only	SCL (D6)		
		<u>be</u> "H", "L", <u>or</u> RD(E) and WF	OPEN". (R/W) are fix	ked to "H" or "	npedance. D0 t L". a cannot be rea			

Pin name	I/O	Description	Number of pins				
CLS	I    Pin that selects the validity/invalidity of the built-in oscillator circuit for display clocks.      CLS="H": Built-in oscillator circuit valid      CLS="L": Built-in oscillator circuit invalid (external input)      When CLS="L". display clocks are input from the CL pin.      When the SED157A series is used for the master/slave configuration, each of the CLS pins is set to the same level together.      Display clock    Master      Built-in oscillator circuit used    "H"      External input    "L"						
M/S	I	Pin that selects the master/slave operation for the SED157A series.The liquid crystal display system is synchronized by outputting the timing signalrequired for the liquid crystal display for the master operation and inputting thetiming signal required for the liquid crystal display for the master operation and inputting theM/S="H": Master operationM/S="H": Master operationM/S="H": Slave operationAccording to the M/S and CLS states, the following table is given.M/SCLFRSYNCFRSDOF	1				
		circuit      circuit        "H"      "H"      Valid      Output      Output      Output					
		"L"InvalidValidInputOutputOutputOutputOutput"L""H"InvalidInvalidInputInputInputInputInput"L"InvalidInvalidInputInputInputInputInput					
		Display clock I/O pin According to the M/S and CLS states, the following table is given. M/S    CLS    CL      "H"    "H"    Output      "L"    Input					
FR	I/O	Liquid crystal alternating current signal I/O pin M/S="H": Output M/S="L": Input When the SED157A series is used for the master/slave configuration, each FR pin is connected.	1				
SYNC	I/O	Liquid crystal synchronizing current signal I/O pin M/S="H": Output M/S="L": Input When the SED157A series is used for the master/slave configuration, each SYNC pin is connected.	2				
DOF	I/O	Liquid crystal display blanking control pin M/S="H": Output M/S="L": Input When the SED157A series is used for the master/slave configuration, each DOF pin is connected.					
IRS	Ι	V5 voltage adjusting resistor selection pin IRS="H": Built-in resistor used IRS="L": Built-in resistor not used. The V5 voltage is adjusted by the VR pin and stand-alone split resistor. Valid only at master operation. The pin is fixed to "H" or "L" at slave operation.	1				
HPM	I	Power supply control pin of the power supply circuit for liquid crystal drive HPM="H": Normal mode HPM="L": High power supply mode Valid only at master operation. The pin is fixed to "H" or "L" at slave operation.	1				

## • Liquid Crystal Drive Pin

Pin name	I/O	Description						
SEG0 to	0	Output pins for the signal are combined	LCD segm d to select	ent drive. Contents on a desired level amon	of the display RAM g VDD, V2, V3 and	and FR V5.	224	
SEG223				Output	voltage	]		
		RAM data	FR	Display normal operation	Display reversal	]		
		Н	Н	Vdd	V2			
		Н	L	V5	V3	-		
		L	Н	V2	Vdd	-		
	LV3V5Power save—VDD	L	L	V3	V5			
COM0 to		Output pins for the to select a desired	LCD comn evel amon	non drive. Scan data g VDD, V1, V4 and V5	and FR signal are	combined	64	
COM63		Scanning	data	FR	Output voltage			
		Н		Н	V5			
		Н		L	Vdd			
		L		Н	V1			
		L		L	V4			
		Power s	ave	—	Vdd			
COMS	0	Indicator dedicated Set to OPEN when When COMS is use to both the master a	not used d for the n	out pin naster/slave configura	ation, the same sig	nal is output	2	

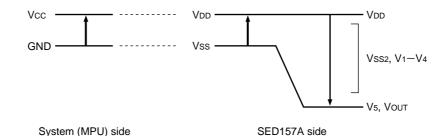
#### • Test Pin

Pin name	I/O	Description	Number of pins
TEST1 to 4, 10 to 13	I/O	IC chip test pin. Fix the pin to "H".	8
TEST5 to 9, 14 to 16	I/O	IC chip test pin. Take into consideration so that the capacity of lines cannot be exhausted by setting the pin to OPEN.	13

## ■ ABSOLUTE MAXIMUM RATINGS

Vss=0 V	unless	specified	otherwise
	41110000	opeeniea	01110111100

Item	l	Symbol	Specif	icatio	on value	Unit
Power supply voltage		Vdd	-0.3	to	+7.0	V
Power supply voltage (2)			-7.0	to	+0.3	
(Based on VDD)	At triple boosting	Vss2	-6.0	to	+0.3	
	At quadruple boosting		-4.5	to	+0.3	
Power supply voltage (3) (Ba	sed on Vdd)	V5, Vout	-22.0	to	+0.3	
Power supply voltage (4) (Ba	sed on Vdd)	V1, V2, V3, V4	V5	to	+0.3	
Input voltage		Vin	-0.3	to	Vdd+0.3	
Output voltage		Vout	-0.3	to	Vdd+0.3	
Operating temperature	Operating temperature		-40	to	+85	°C
Storage temperature	ТСР	TSTR	-55	to	+100	
	Bare chip		-55	to	+125	



- Notes: 1. The values of the Vss<sub>2</sub>, V<sub>1</sub> to V<sub>5</sub>, and Vout voltages are based on VDD=0 V.
  - 2. The V1, V2, V3, and V4 voltages must always satisfy the condition of  $VDD \ge V1 \ge V2 \ge V3 \ge V4 \ge V5$ .
  - 3. Insure that voltage levels Vss₂ and Vou⊤ are always such that the relationship of VDD≥Vss≥Vss₂≥ Vou⊤ is maintained.
  - 4. When LSI is used exceeding the absolute maximum ratings, the LSI may be damaged permanently. Besides, it is desirable that the LSI should be used in the electrical characteristics condition for normal operation. If this condition is exceeded, the LSI may malfunction and have an adverse effect on the reliability of the LSI.

## ■ DC Characteristics

Vss=0 V, Vdd=3.0 V  $\pm$  10%, and Ta=–40 to 85°C

			<b>A</b> 11/1		Spe	cification v		Applicable	
	ltem	Symbol	Conditio	on	Min.	Тур.	Max.	Unit	pin
Operating voltage	Recommended operation	Vdd			2.7	_	3.3	V	VDD
(1)	Operable	Vdd			1.8	_	5.5		Vdd
Operating voltage	Recommended operation	VSS2	(Based on VDD)		-3.3	—	-2.7		VSS2
(2)	Operable	Vss2	(Based on VDD)		-6.0	—	-1.8		VSS2
Operating	Operable	V5	(Based on VDD)		-18.0	_	-4.5	1	V5
voltage	Operable	V1, V2	(Based on VDD)		0.4×V5	—	Vdd		V1, V2
(3)	Operable	V3, V4	(Based on VDD)		V5	—	0.6×V5		V3, V4
High level ir	nput voltage	VIHC			0.8×Vdd	_	Vdd		
Low level in	put voltage	VILC			Vss	—	0.2×Vdd		
High level o	utput voltage	Vонс	Іон=–0.5mA		0.8×Vdd	_	Vdd		
Low level ou	utput voltage	Volc	lo∟=0.5mA		Vss	—	0.2×Vdd		
Input leak c	urrent	lu	VIN=VDD or Vss		-1.0	_	1.0	μA	
Output leak	current	ILO			-3.0	—	3.0		
Liquid crysta	al driver	Ron	Ta=25°C	V5=-14.0V		2.0	3.5	KΩ	SEGn
On resist	tance		(Based on VDD)	V5=-8.0V	—	3.2	5.4		COMn
Static currer	nt consumption	Issq		•	_	0.01	5	μA	Vss, Vss2
Output leak	current	l5Q	V5=-18.0V (Based on	Vdd)	—	0.01	15		V5
Input pin ca	pacity	Сі	Ta=25°C, f=1MHz			5.0	8.0	pF	
Oscillating frequency	Built-in oscillation	fosc	Ta=25°C		18	22	26	kHz	
	External input	fc∟			4.5	5.5	6.5		CL

	lt a see	Symbol		_	Spe	Specification value			Applicable
	Item	Symbol	Conditio	n	Min.	Тур.	Max.	Unit	pin
circuit	Input voltage	Vss2	At triple boosting (Based on VDD)		-6.0	_	-1.8	V	Vss2
supply ci		Vss2	At quadruple boosting (Based on VDD)		-5.0	—	-1.8		Vss2
Ins	Boosting output voltage	Vout	(Based on VDD)		-20.0	—	_	]	Vout
power	Voltage adjusting circuit operating voltage	Vout	(Based on VDD)		-20.0	_	-6.0		Vout
Built-in p	V/F circuit operating voltage	V5	(Based on VDD)	(Based on VDD)		—	-4.5	1	V5
ы	Reference voltage	Vreg0	Ta=25°C,	–0.05%/°C	-2.04	-2.10	-2.16	1	

11

Dynamic current consumption value (1) During display operation and built-in power supply OFF Current values dissipated by the whole IC when the external power supply is used

Display	All	White	
---------	-----	-------	--

Display All White Ta											
Item Sy	Symbol	Condition	Spec	ification v	Unit	Domorko					
	Symbol Condition	Condition	Min.	Тур.	Max.	Unit	Remarks				
Dynamic current	IDD	VDD=5.0V, V5-VDD=-11.0V	—	25	42	μA					
consumption	(1)	VDD=3.0V, V5-VDD=-11.0V	—	25	42						

Display Checker Pattern Ta=25°C										
Item Symbo	Condition	Spec	ification v	l lmit	Domorko					
	Symbo	Condition	Min.	Тур.	Max.	Unit	Remarks			
Dynamic current	IDD	VDD=5.0V, V5-VDD=-11.0V	—	38	64	μA				
consumption	(1)	VDD=3.0V, V5-VDD=-11.0V	—	38	64					

Dynamic current consumption value (2) During display operation and built-in power supply ON Current values dissipated by the whole IC containing the built-in power supply circuit

**Display Checker Pattern** 

ltom	Cumb a	Condi	Spec	ification v	Unit	Remarks		
Item	Symbo	Condi	tion	Min.	Тур.	Max.	Unit	Remarks
Dynamic current	IDD	Vdd=5.0V,	Normal mode	_	92	154	μA	
consumption	(2)	Triple boosting						
		V5-VDD=-11.0V	High power mode	_	242	405	1	
		Vdd=3.0V,	Normal mode		129	216		
		Quadruple boosting						
		V5–Vdd=–11.0V	High power mode	_	310	518		

#### **Display Checker Pattern**

ltom	Sumbo	Conc	Spec	ification v	Unit	Remarks		
Item	Symbo	Conc	attion	Min.	Тур.	Max.	Unit	Remarks
Dynamic current	IDD	Vdd=5.0V,	Normal mode	—	132	221	μA	
consumption	(2)	Triple boosting						
		V5-VDD=-11.0V	High power mode	_	280	468		
		Vdd=3.0V,	Normal mode	_	167	279		
		Quadruple boosting						
		V5-VDD=-11.0V	High power mode	_	350	585		

Current consumption at power save <code>Vss=0V</code> and <code>Vdd= 3.0 V \pm 10%</code>

							Ta=25°C
Item	Symbol	Condition	Spec	ification v	Unit	Domorika	
			Min.	Тур.	Max.	Unit	Remarks
Sleep state	IDDS1		—	0.01	5	μΑ	
Stand-by state	IDDS2			4	8		

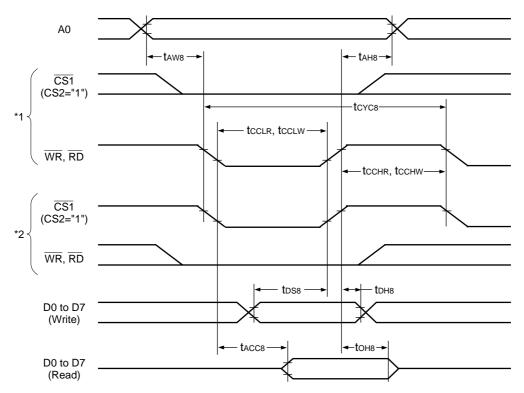
## **EPSON**

Ta=25°C

Ta=25°C

## ■ TIMING CHARACTERISTICS

• System bus read/write characteristics 1 (80 series MPU)



				<b>b</b>	to 5.5V, Ta=–∕ <b>tion value</b>	
Item	Signal	Symbol	Condition	Min.	Max.	Unit
Address hold time	A0	tAH8		0	_	ns
Address setup time		tAW8		0	_	
System cycle time	A0	tCYC8		333	—	
Control L pulse width (WR)	WR	tCCLW		30	—	
Control L pulse width (RD)	RD	tCCLR		70	_	
Control H pulse width (WR)	WR	tcchw		30	_	
Control H pulse width (RD)	RD	<b>t</b> CCHR		30	—	
Data setup time	D0 to D7	tDS8		30	_	
Data hold time		tDH8		10	—	
RD access time		tACC8	CL=100pF		70	
Output disable time		tOH8		5	50	

[VDD=2.7V to 4.5V. Ta=-40 to 85°C]

	<u>.</u>		Condition	Specifica	tion value	
Item	Signal	Symbol		Min.	Max.	Unit
Address hold time	A0	tah8		0	_	ns
Address setup time		tAW8		0		
System cycle time	A0	tCYC8		500	—	
Control L pulse width (WR)	WR	tCCLW		60		
Control L pulse width (RD)	RD	tCCLR		120	_	
Control H pulse width (WR)	WR	tCCHW		60	_	
Control H pulse width (RD)	RD	<b>t</b> CCHR		60	—	
Data setup time	D0 to D7	tDS8		40	_	
Data hold time		tdh8		15		
RD access time		tACC8	CL=100pF	—	140	
Output disable time		tOH8		10	100	

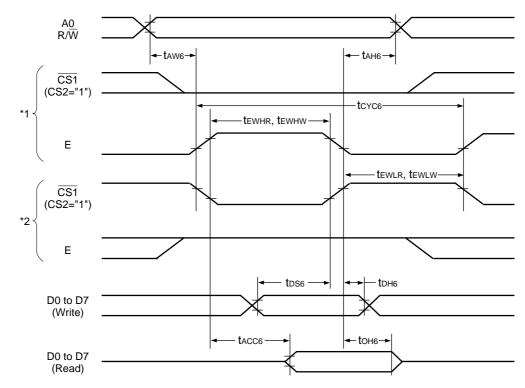
[VDD=1.8V to 2.7V, Ta=-40 to 85°C]

	<u>.</u>			Specification value		
Item	Signal	Symbol	Condition	Min.	Max.	Unit
Address hold time	A0	tah8		0		ns
Address setup time		tAW8		0	—	
System cycle time	A0	tCYC8		1000	—	
Control L pulse width (WR)	WR	tCCLW		120	_	
Control L pulse width (RD)	RD	tCCLR		240	—	
Control H pulse width (WR)	WR	tCCHW		120	—	
Control H pulse width (RD)	RD	tCCHR		120		
Data setup time	D0 to D7	tDS8		80	—	
Data hold time		tDH8		30	—	
RD access time		tACC8	CL=100pF		280	
Output disable time		tOH8		10	200	

Notes: 1. This is the case of accessing by  $\overline{WR}$  and  $\overline{RD}$  when  $\overline{CS1}$  = "L". 2. This is the case of accessing by  $\overline{CS1}$  when  $\overline{WR}$  and  $\overline{RD}$  = "L".

 The rise and fall times (tr and tr) of the input signal are specified for less than 15 ns. When using the system cycle time at high speed, they are specified for (tr+tf) ≤ (tCYC8–tCCLW–tCCHW) or (tr+tf) ≤ (tCYC8–tCCLR–tCCHR). 4. All timings are specified based on the 20 and 80% of VDD.

5.tccLW and tccLR are specified for the overlap period when  $\overline{CS1}$  is at "L" (CS2= "H") level and  $\overline{WR}$ ,  $\overline{RD}$  are at the "L" level.



## • System bus read/write characteristics 2 (68 series MPU)

				r	[VDD=4.5V 1	to 5.5V, Ta=–4	10 to 85°C]
		Signal	Complete	O a mallitha m	Specifica	tion value	
Item		Signal	Symbol	Condition	Min.	Max.	Unit
Address hold time		A0	tAH6		0	_	ns
Address setup time			tAW6		0	—	
System cycle time			tCYC6		333	—	
Data setup time		D0 to D7	tDS6		30	_	
Data hold time			tDH6		10	—	
Access time			tACC6	CL=100pF	_	70	
Output disable time			tOH6		10	50	
Enable H pulse width	Read	E	tewhr		70	_	
	Write		tewhw		30	—	
Enable L pulse width	Read	E	tEWLR		30	_	
	Write		tEWLW		30	_	

#### [VDD=2.7V to 4.5V, Ta=-40 to 85°C]

lt a m		0:	0 miles l	O a malifilia m	Specifica	tion value	11
Item		Signal	Symbol	Condition	Min.	Max.	Unit
Address hold time		A0	tAH6		0	—	ns
Address setup time			tAW6		0	_	
System cycle time			tCYC6		500	—	
Data setup time		D0 to D7	tDS6		40	—	
Data hold time			tDH6		15	_	
Access time			tACC6	CL=100pF	—	140	
Output disable time			tOH6		10	100	
Enable H pulse width	Read	E	tewhr		120	—	
	Write		tewhw		60	_	
Enable L pulse width	Read	E	tewlr		60	_	
	Write		tewlw		60	_	

#### [VDD=1.8V to 2.7V, Ta=-40 to 85°C]

literes		Signal Symbol	Cumb al	Condition	Specifica	tion value	Unit
Item		Signal Symbol		Condition	Min.	Max.	Unit
Address hold time		A0	tAH6		0	—	ns
Address setup time			tAW6		0	_	
System cycle time			tCYC6		1000	—	
Data setup time		D0 to D7	tDS6		80	—	
Data hold time			tDH6		30	_	
Access time			tACC6	CL=100pF	—	280	
Output disable time			tOH6		10	200	
Enable H pulse width	Read	E	tewhr		240	—	
	Write		tewhw		120	—	
Enable L pulse width	Read	E	tewlr		120	—	
	Write		tewlw		120		

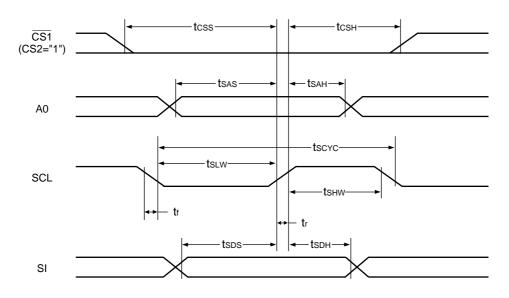
Notes: 1. This is the case of accessing by <u>E</u> when  $\overline{CS1} = "L"$ .

2. This is the case of accessing by CS1 when E = "H". 3. The rise and fall times (tr and tr) of the input signal are specified for less than 15 ns. When using the system cycle time at high speed, they are specified for  $(tr+tf) \le (tCYC6-tEWLW-tEWHW)$  or  $(tr+tf) \le (tCYC6-tEWLR-tEWHR)$ .

4. All timings are specified based on the 20 and 80% of VDD.

5. tEWLW and tEWLR are specified for the overlap period when  $\overline{CS1}$  is at "L" (CS2 = "H") level and E is at the "H" level.

#### Serial interface



#### [VDD=4.5V to 5.5V, Ta=-40 to 85°C]

ltem	Signal	Symbol	Condition	Specification value		Unit
	Signal	Symbol		Min.	Max.	
Serial clock cycle	SCL	tSCYC		200	—	ns
SCL "H" pulse width		tshw		75		
SCL "L" pulse width		tSLW		75		
Address setup time	A0	tsas		50	—	1
Address hold time		<b>t</b> SAH		100		
Data setup time	SI	tSDS		50	—	]
Data hold time		<b>t</b> SDH		50		
CS-SCL time	CS	tcss		100	—	]
		tCSH		100		

#### [VDD=2.7V to 4.5V, Ta=-40 to 85°C]

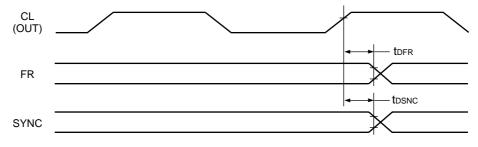
				Creation	Unit	
Item	Signal	Symbol	Condition	Specifica		
	Signal	Symbol		Min.	Max.	Onic
Serial clock cycle	SCL	tSCYC		250	—	ns
SCL "H" pulse width		tshw		100	_	
SCL "L" pulse width		tSLW		100	_	
Address setup time	A0	tSAS		150	—	
Address hold time		tSAH		150	_	
Data setup time	SI	tSDS		100	—	7
Data hold time		tSDH		100	_	
CS-SCL time	CS	tCSS		150	—	
		tCSH		150		

#### [VDD=1.8V to 2.7V, Ta=-40 to 85°C]

Item	Circul	Cumhal	Condition	Specifica	Specification value	
	Signal	Symbol	Condition	Min.	Max.	- Unit
Serial clock cycle	SCL	tSCYC		400	—	ns
SCL "H" pulse width		tshw		150	_	
SCL "L" pulse width		tsLw		150	_	
Address setup time	A0	tsas		250	_	_
Address hold time		tSAH		250	_	
Data setup time	SI	tSDS		150	—	_
Data hold time		tSDH		150	_	
CS-SCL time	CS	tCSS		250	—	_
		tCSH		250	_	

Notes: 1. The rise and fall times (tr and tf) of the input signal are specified for less than 15 ns. 2. All timings are specified based on the 20 and 80% of VDD.

#### Display control output timing



#### [VDD=4.5V to 5.5V, Ta=-40 to 85°C]

ltem	Signal	Symbol	nbol Condition	Sp	Unit		
	Signal Symbol	Condition	Min.	Тур.	Max.	Unit	
FR delay time	FR	tDFR	C∟=50pF		10	40	ns
SYNC delay time	SYNC	<b>t</b> DSNC	C∟=50pF	—	10	40	ns

[VDD=2.7V to 4.5V, Ta=-40 to 85°C]

Item	Signal	Signal Symbol	Condition	Sp	Unit		
	Signal Symbol	Condition	Min.	Тур.	Max.	Unit	
FR delay time	FR	tDFR	C∟=50pF	—	20	80	ns
SYNC delay time	SYNC	<b>t</b> DSNC	CL=50pF		20	80	ns

[VDD=1.8V to 2.7V, Ta=-40 to 85°C]

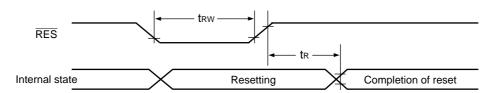
Item	Signal Syml	Symbol	Symbol	Symbol	Condition	Sp	ecification va	lue	Unit
		Symbol	Condition	Min.	Тур.	Max.	Unit		
FR delay time	FR	tDFR	C∟=50pF	_	50	200	ns		
SYNC delay time	SYNC	<b>t</b> DSNC	CL=50pF		50	200	ns		

Notes: 1. Valid only when the master mode is selected.

 All timings are specified based on the 20 and 80% of VDD.
 Pay attention not to cause delays of the timing signals CL, FR and SYNC to the salve side by wiring resistance, etc., while master/slave operations are in progress. If these delays occur, indication failures such as flickering may occur.

## **SED157A Series**

#### • Reset input timing



[VDD=4.5V to 5.5V, Ta=-40 to 85°C]

	<u>.</u>		Symbol Condition	Spe			
ltem	Signal Symbol	Symbol		Min.	Тур.	Max.	Unit
Reset time		tR		—	—	0.5	μs
Reset "L" pulse width	RES	trw		0.5	_	—	

[VDD=2.7V to 4.5V, Ta=-40 to 85°C]

			Spe				
ltem	Signal	Symbol	Condition	Min.	Тур.	Max.	Unit
Reset time		tR		—	_	1	μs
Reset "L" pulse width	RES	trw		1	_	—	

[VDD=1.8V to 2.7V, Ta=-40 to 85°C]

	<u>.</u>			Sp			
ltem	Signal	Symbol	Condition	Min.	Тур.	Max.	Unit
Reset time		tR		_		1.5	μs
Reset "L" pulse width	RES	trw		1.5	—	—	

Note: All timings are specified based on the 20 and 80% of VDD.

#### NOTICE:

No part of this material may be reproduced or duplicated in any form or by any means without the written permission of Seiko Epson. Seiko Epson reserves the right to make changes to this material without notice. Seiko Epson does not assume any liability of any kind arising out of any inaccuracies contained in this material or due to its application or use in any product or circuit and, further, there is no representation that this material is applicable to products requiring high level reliability, such as, medical products. Moreover, no license to any intellectual property rights is granted by implication or otherwise, and there is no representation or warranty that anything made in accordance with this material will be free from any patent or copyright infringement of a third party. This material or portions thereof may contain technology or the subject relating to strategic products under the control of the Foreign Exchange and Foreign Trade Law of Japan and may require an export license from the Ministry of International Trade and Industry or other approval from another government agency.

© Seiko Epson Corporation 2000 All right reserved.

All other product names mentioned herein are trademarks and/or registered trademarks of their respective companies.

#### SEIKO EPSON CORPORATION

ELECTRONIC DEVICES MARKETING DIVISION

#### IC Marketing & Engineering Group

**ED International Marketing Department I (Europe, U.S.A)** 421-8 Hino, Hino-shi, Tokyo 191-8501, JAPAN Phone: 042-587-5812 FAX: 042-587-5564

**ED International Marketing Department II (ASIA)** 421-8 Hino, Hino-shi, Tokyo 191-8501, JAPAN Phone: 042-587-5814 FAX: 042-587-5110 Electronic devices information on the Epson WWW server. http://www.epson.co.jp/device/



First issue February, 2000 Printed in Japan (I)